



(19) Europäisches Patentamt
European Patent Office
Office européen des brevets



(11) Publication number: 0 459 771 A3

(12)

EUROPEAN PATENT APPLICATION

(21) Application number: 91304828.6

(51) Int. Cl.⁵: H01L 29/52, H01L 29/784,
H01L 21/74, H01L 21/3205,
H01L 27/092

(22) Date of filing: 29.05.91

(30) Priority: 31.05.90 JP 139618/90
08.08.90 JP 208145/90

(43) Date of publication of application:
04.12.91 Bulletin 91/49

(64) Designated Contracting States:
AT BE CH DE DK ES FR GB GR IT LI LU NL SE

(68) Date of deferred publication of search report:
05.02.92 Bulletin 92/06

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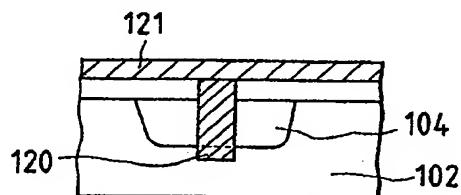
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(54) Electrode for semiconductor device and method for producing the same.

(57) There is provided a semiconductor device with very small functional elements, which can be constructed by necessary minimum components without any unnecessary surface area, thus being capable of significantly reducing the layout area and adapted for achieving a fine geometry and a high level of integration. The semiconductor device is provided with a first semiconductor area of a first conductive type (for example a p⁻ well) and a second semiconductor area formed on or under the first semiconductor area and having a second conductive type different from the first conductive type (for example a source or drain area), in which an electrode electrically connected to the first semiconductor area is formed through the second semiconductor area, and the first and second semiconductor areas are shortcircuited by the above-mentioned electrode.

FIG. 4A



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EP 91 30 4828

DOCUMENTS CONSIDERED TO BE RELEVANT			CLASSIFICATION OF THE APPLICATION (Int. Cl.5)
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	H01L29/52 H01L29/784 H01L21/74 H01L21/3205 H01L27/092
Y	PATENT ABSTRACTS OF JAPAN vol. 13, no. 117 (E-731)22 March 1989 & JP-A-63 288 057 (SANYO ELECTRIC CO LTD) 25 November 1988 * abstract * ----	1,2,3,10	H01L29/52 H01L29/784 H01L21/74 H01L21/3205 H01L27/092
Y	PATENT ABSTRACTS OF JAPAN vol. 8, no. 123 (E-249)8 June 1984 & JP-A-59 035 463 (TOKYO SHIBAURA DENKI K.K.) 27 February 1984 * abstract * ----	1,2,3,10	
X	PATENT ABSTRACTS OF JAPAN vol. 10, no. 150 (E-408)31 May 1986 & JP-A-61 008 969 (NIPPON DENKI K.K.) 16 January 1986 * abstract * ----	1,2	
X	GB-A-2 055 247 (ITT INDUSTRIES, INC.) * the whole document * ----	1,2	
A	PATENT ABSTRACTS OF JAPAN vol. 13, no. 581 (E-865)21 December 1989 & JP-A-1 244 646 (MITSUBISHI ELECTRIC CORP) 29 September 1989 * abstract * ----	1,2,8,9	TECHNICAL FIELDS SEARCHED (Int. Cl.5)
A	EP-A-0 284 065 (NEC CORPORATION) * abstract; figure 6 * ----	3,10	H01L
A	PATENT ABSTRACTS OF JAPAN vol. 10, no. 328 (C-383)7 November 1986 & JP-A-61 136 682 (NEC CORP) 24 June 1986 * abstract * -----	8,9,10	
The present search report has been drawn up for all claims			
Place of search THE HAGUE	Date of completion of the search 09 DECEMBER 1991	Examiner MIMOUN B.J.	
CATEGORY OF CITED DOCUMENTS		T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application L : document cited for other reasons A : member of the same patent family, corresponding document	
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